

**SANYO**

No.3104A

**2SC4218**

NPN Triple Diffused Planar Silicon Transistor  
 Color TV Chroma Output,  
 High-Voltage Driver Applications

**Features**

- High breakdown voltage
- Small reverse transfer capacitance and excellent high frequency characteristics
- Adoption of FBET process

**Absolute Maximum Ratings at Ta = 25°C**

			unit
Collector to Base Voltage	V <sub>CB0</sub>	300	V
Collector to Emitter Voltage	V <sub>CEO</sub>	300	V
Emitter to Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	I <sub>C</sub>	100	mA
Peak Collector Current	i <sub>cp</sub>	200	mA
Collector Dissipation	P <sub>C</sub>	500	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

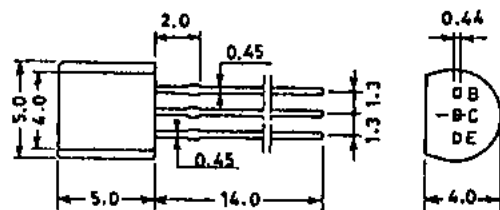
**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 200V, I <sub>E</sub> = 0			0.1	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V, I <sub>C</sub> = 0			0.1	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> = 10V, I <sub>C</sub> = 1mA	60		320	
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 30V, I <sub>C</sub> = 10mA		70		MHz
C-E Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA			0.6	V
B-E Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1mA			1.0	V
C-B Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 10μA, I <sub>E</sub> = 0	300			V
C-E Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 1mA, R <sub>BE</sub> = ∞	300			V
E-B Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 10μA, I <sub>C</sub> = ∞	5			V
Output Capacitance	c <sub>ob</sub>	V <sub>CB</sub> = 30V, f = 1MHz		1.5		pF
Reverse Transfer Capacitance	c <sub>re</sub>	V <sub>CB</sub> = 30V, f = 1MHz		1.0		pF

※ : The 2SC4218 is classified by 1mA h<sub>FE</sub> as follows :

60	D	120	100	E	200	160	F	320
----	---	-----	-----	---	-----	-----	---	-----

**Case Outline 2003A**  
 (unit : mm)



JEDEC: TO-92

EIAJ: SC-43

SANYO: NP

B: Base

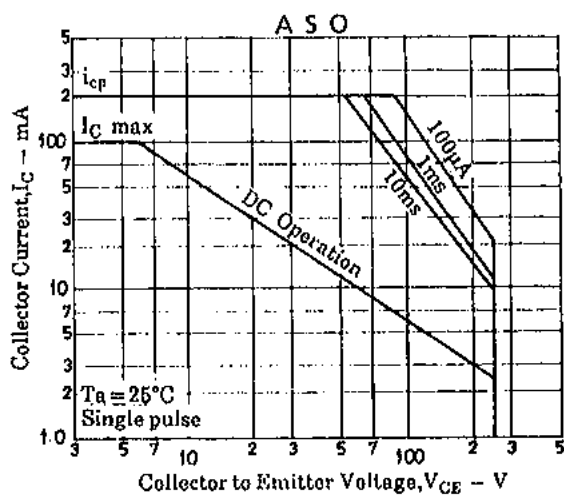
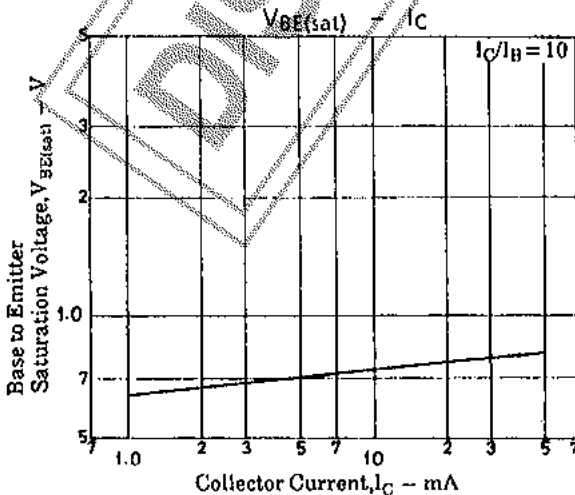
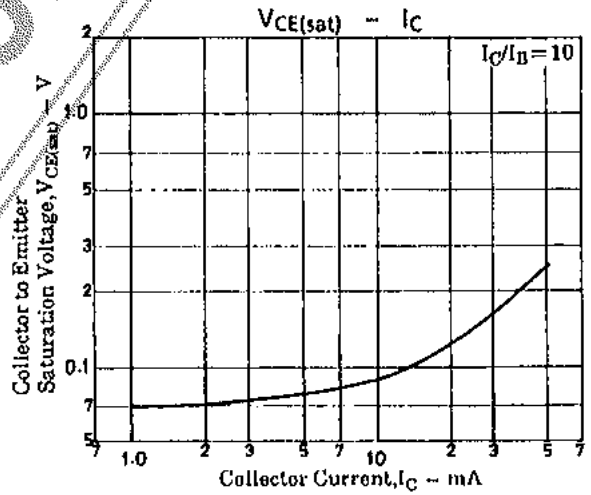
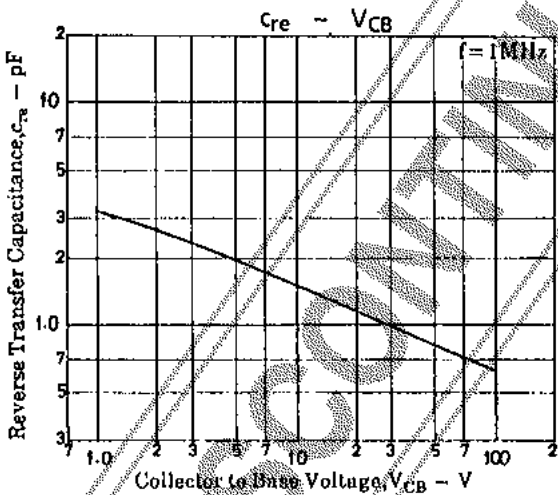
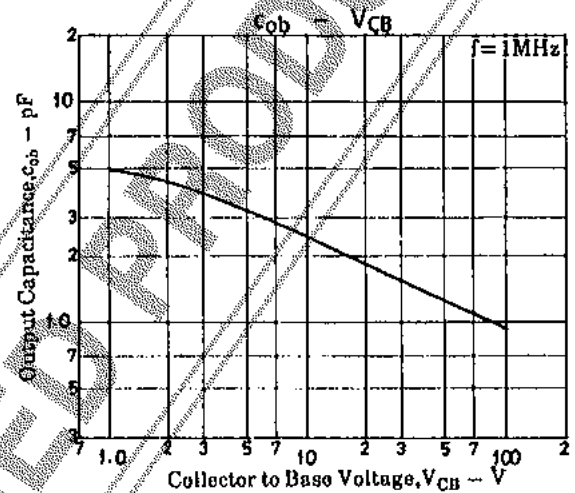
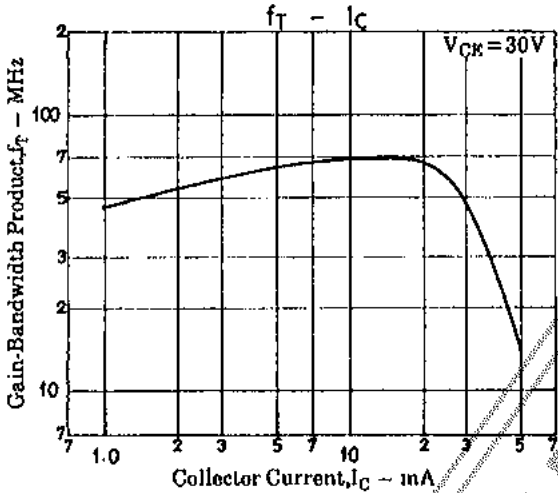
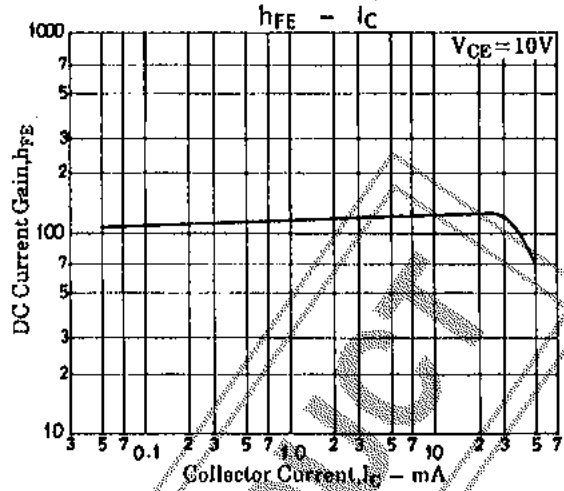
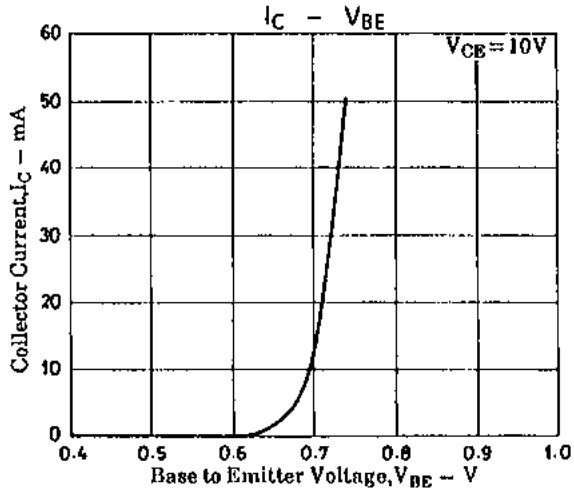
C: Collector

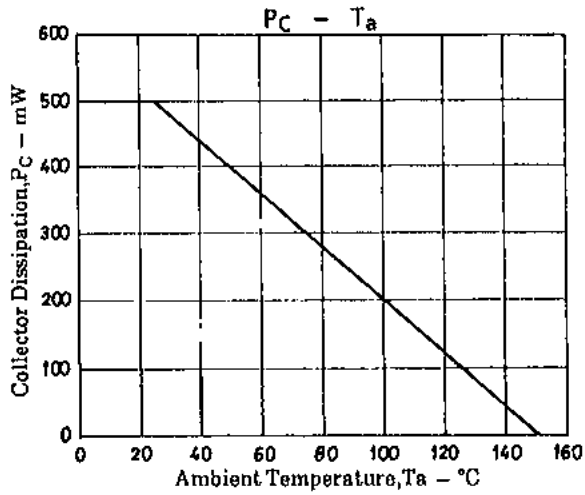
E: Emitter

Specifications and information herein are subject to change without notice.

**SANYO Electric Co., Ltd. Semiconductor Overseas Marketing Div.**  
 Natsume Bldg., 18-6, 2 chome, Yushima, Bunkyo-ku, TOKYO 113 JAPAN

5070MO/N149MO,TS No.3104-1/3





The application circuit diagrams and circuit constants herein are included as an example and provide no guarantee for designing equipment to be mass-produced. The information herein is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use, nor for any infringements of patents or other rights of third parties which may result from its use.

DISCONTINUED PRODUCT

This datasheet has been downloaded from:

[www.DatasheetCatalog.com](http://www.DatasheetCatalog.com)

Datasheets for electronic components.